**Vishay Semiconductors** 



## Ultrafast Rectifier, 2 A FRED Pt®



Cathode O Anode

### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub>	2 A					
V <sub>R</sub>	100 V, 200 V					
V <sub>F</sub> at I <sub>F</sub>	0.79 V					
I <sub>FSM</sub>	40 A					
t <sub>rr</sub> (typ.)	23 ns					
T <sub>J</sub> max.	175 °C					
Package	SMP (DO-220AA)					
Circuit configuration	Single					

### FEATURES

- Very low profile typical height of 1.0 mm
- Ideal for automated placement
- Low forward voltage drop, low power losses
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- For PFC, CRM snubber operation
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **TYPICAL APPLICATION**

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial and automotive applications.

### **MECHANICAL DATA**

Case: SMP (DO-220AA)

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per

J-STD-002, meets JESD 201 class 2 whisker test **Polarity:** color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Deale repetitive reverse veltage	VS-2ENH01HM3	N/		100	V			
Peak repetitive reverse voltage	VS-2ENH02HM3	V <sub>RRM</sub>		200	v			
Average rectified forward current		I <sub>F(AV)</sub>	T <sub>C</sub> = 158 °C	2	٨			
Non-repetitive peak surge current		I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 10 ms sine pulse	40	A			
Operating junction and storage temperatures		T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25$ °C unless otherwise specified)								
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage,	VS-2ENH01HM3	V <sub>BR</sub> ,	I <sub>B</sub> = 100 μA	100	-	-		
blocking voltage	VS-2ENH02HM3	V <sub>R</sub>	i <sub>R</sub> = 100 μΑ	200	-	-		
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 2 A	-	0.94	1.00		
			I <sub>F</sub> = 2 A, T <sub>J</sub> = 150 °C	-	0.79	0.84		
Reverse leakage current		I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	-	2		
			$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	20	μA	
Junction capacitance		CT	V <sub>R</sub> = 200 V	-	8	-	pF	

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1



FREE



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, dI_F/dt = 10$	00 A/µs, V <sub>R</sub> = 30 V	-	23	-	
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A		-	-	28	
		T <sub>J</sub> = 25 °C		-	16	-	ns
		T <sub>J</sub> = 125 °C		-	25	-	
Peak receivery ourrent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	$I_F = 2 A$	-	2.0	-	A nC
Peak recovery current		T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 200 A/µs V <sub>B</sub> = 100 V	-	3.1	-	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	15	-	
		T <sub>J</sub> = 125 °C		-	37	-	no

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C	
Thermal resistance, junction to mount		R <sub>thJM</sub> <sup>(1)</sup>	Infinite heatsink	-	7	9	°C/W	
Thermal resistance, junction to ambient		R <sub>thJA</sub>	PCB footprint 4.8 mm x 4.8 mm	-	107	-	0/10	
VS-2ENH01HM3			Case style SMP (DO-220AA)	2H1				
Marking device	VS-2ENH02HM3		Case style Sivir (DO-220AA)	2H2				

#### Note

<sup>(1)</sup> Thermal resistance junction to mount follows JEDEC<sup>®</sup> 51-14 transient dual interface test method (TDIM)

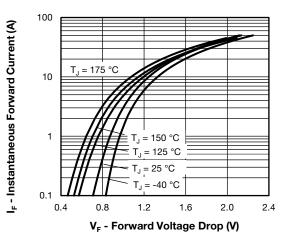


Fig. 1 - Typical Forward Voltage Drop Characteristics

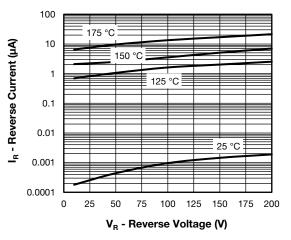


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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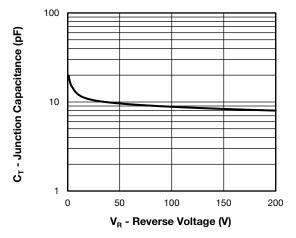


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

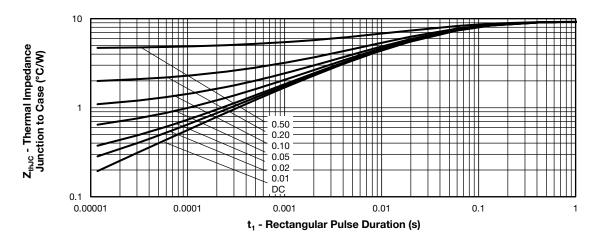


Fig. 4 - Transient Thermal Impedance, Junction to Case

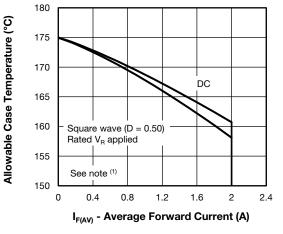


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

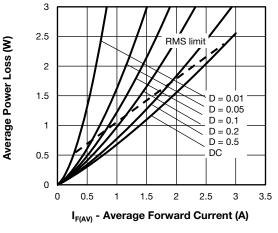


Fig. 6 - Forward Power Loss Characteristics

Revision: 28-Jan-2021

3

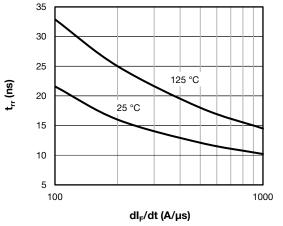
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125 °C

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1000



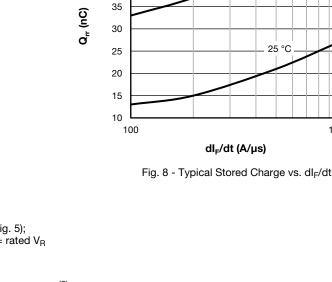
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Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

#### Note

SHAY

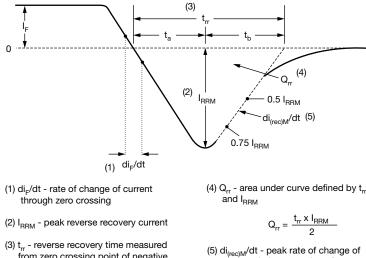
- <sup>(1)</sup> Formula used:  $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$ ;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig. 5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$



current during t<sub>b</sub> portion of t<sub>rr</sub>

50 45

40



from zero crossing point of negative

going I<sub>F</sub> to point where a line passing through 0.75  $I_{RRM}$  and 0.50  $I_{RRM}$  extrapolated to zero current.

Fig. 9 - Reverse Recovery Waveform and Definitions



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### **ORDERING INFORMATION TABLE**

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SHAY

Device code	VS-	2	Е	N	н	02	н	М3	
		(2)	(3)	(4)	(5)	(6)	(7)	(8)	1
	1	- Visl	nay Sen	niconduo	ctors pro	oduct	0	0	
	2		•	ng (2 = 2					
	3	- Circ	uit conf	iguratior	ו:				
		E =	single o	liode					
	4	- N =	SMP pa	ackage					
	5	- Pro	cess typ	e,					
		H =	ultrafas	t recove	ery				
	6	- Vol	tage coo	de (02 =	200 V)				
	7	- H=	AEC-Q	101 qua	lified				
	8	- M3	= halog	en-free,	RoHS-0	complia	nt, and	termina	tions lea

ORDERING INFORMATION (Example)								
PREFERRED P/N	PREFERRED PACKAGE CODE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-2ENH01HM3/84A	84A	3000	7" diameter plastic tape and reel					
VS-2ENH01HM3/85A	85A	10 000	13" diameter plastic tape and reel					
VS-2ENH02HM3/84A	84A	3000	7" diameter plastic tape and reel					
VS-2ENH02HM3/85A	85A	10 000	13" diameter plastic tape and reel					

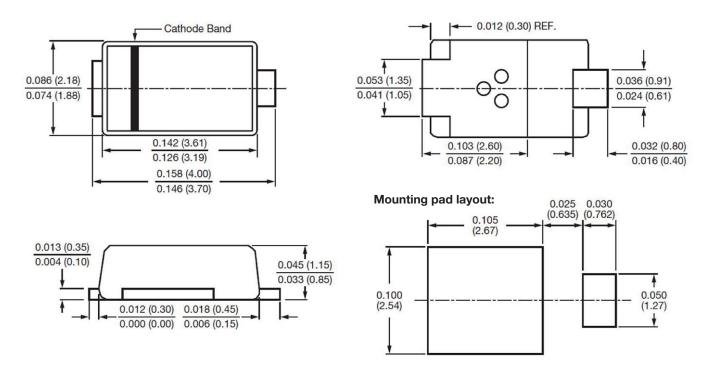
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96547					
Part marking information	www.vishay.com/doc?96574					
Packaging information	www.vishay.com/doc?88869					
SPICE model	www.vishay.com/doc?96551					



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# SMP (DO-220AA)

### **DIMENSIONS** in inches (millimeters)





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